

R-C Thermal Model Parameters

DESCRIPTION

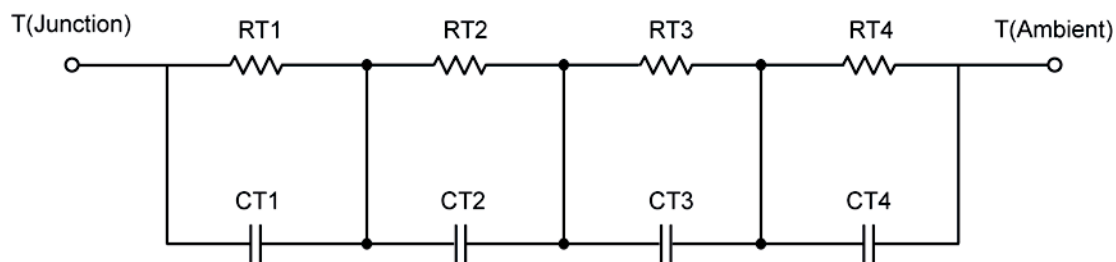
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

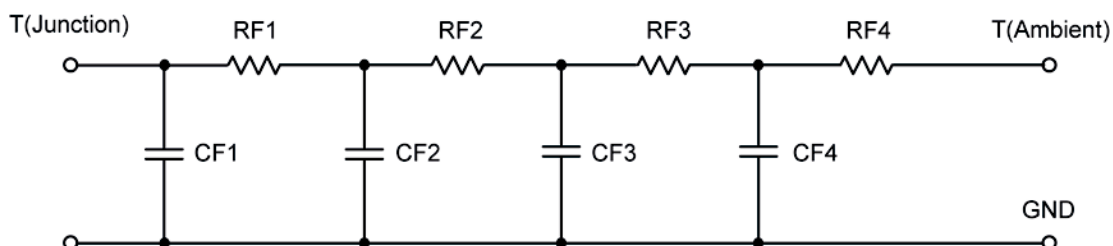
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	12.8558	N/A	7.1164
RT2	5.5330	N/A	686.8858 m
RT3	14.4998	N/A	4.0471
RT4	51.5942	N/A	9.1031
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	46.4471 m	N/A	9.8824 m
CT2	9.6323 m	N/A	1.0122 m
CT3	175.2058 m	N/A	1.4854
CT4	1.1057	N/A	103.5798 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	6.8571	N/A	1.4742
RF2	19.1774	N/A	9.0483
RF3	15.0203	N/A	8.2299
RF4	44.3669	N/A	2.0735
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	6.0118 m	N/A	1.9613 m
CF2	28.4945 m	N/A	9.7679 m
CF3	204.8711 m	N/A	143.6799 m
CF4	1.1248	N/A	1.9446

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

